DERWENT-ACC-NO:

2003-655221

DERWENT-WEEK:

200514

COPYRIGHT 2005 DERWENT INFORMATION LTD

TITLE:

Cvd apparatus using plasma

INVENTOR: PARK, Y S

PATENT-ASSIGNEE: KOKUSAI ELECTRIC KOREA[KOKZ] , KOOKJE ELECTRIC KOREA CO

LTD [KOOKN]

PRIORITY-DATA: 2001KR-0070914 (November 15, 2001)

PATENT-FAMILY:

PUB-NO PUB-DATE LANGUAGE PAGES
MAIN-IPC
KR 450286 B October 15, 2004 N/A 000
H01L 021/205
KR 2003040581 A May 23, 2003 N/A 001
H01L 021/205

APPLICATION-DATA:

PUB-NO APPL-DESCRIPTOR APPL-NO APPL-

DATE

KR 450286B N/A 2001KR-0070914

November 15, 2001

KR 450286B Previous Publ. KR2003040581 N/A

KR2003040581A N/A 2001KR-0070914

November 15, 2001

INT-CL (IPC): H01L021/205

ABSTRACTED-PUB-NO: KR2003040581A

BASIC-ABSTRACT:

NOVELTY - A CVD(Chemical Vapor Deposition) apparatus using plasma is provided

to reduce a deposition time and improve the uniformity of a surface of a wafer

by installing a plasma generator in the inside of a process chamber.

DETAILED DESCRIPTION - A <u>boat</u> (300) is installed within a process chamber (200).

A plurality of wafers are loaded into the boat. A shower head(400) is used for

injecting a process gas to the <u>wafers</u> loaded into the <u>boat</u>. A plasma generator(500) is installed within the <u>shower head</u> in order to form the process

gas injected from the shower head to a state of plasma. The shower head is

installed in the inside of the process chamber. A gas induction space is formed by the <u>shower head</u> and a sidewall of the process chamber. A gas induction portion(600) supplies the process gas into the gas induction space of the shower head.

CHOSEN-DRAWING: Dwg.1/10

TITLE-TERMS: CVD APPARATUS PLASMA

DERWENT-CLASS: U11 V05

EPI-CODES: U11-C09B; U11-C09C; V05-F04E; V05-F05C; V05-F05E3; V05-F08D1;

